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Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Low threshold voltage
- · Very fast switching
- · Trench MOSFET technology
- · ElectroStatic Discharge (ESD) protection

3. Applications

- · Relay driver
- · High-speed line driver
- · Low-side loadswitch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V	
V_{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	190	mA	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 190 \text{ mA}; T_j = 25 \text{ °C}$		-	3	4.5	Ω	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



60 V, N-channel Tench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D -
2	S	source		
3	D	drain	TO-236AB (SOT23)	G S S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package	je				
	Name	Description	Version			
NX138AK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
NX138AK	AP%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	190	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	120	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	765	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	265	mW
			[1]	-	325	mW
		T _{sp} = 25 °C		-	1.33	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode					'
Is	source current	T _{amb} = 25 °C	[1]	-	190	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

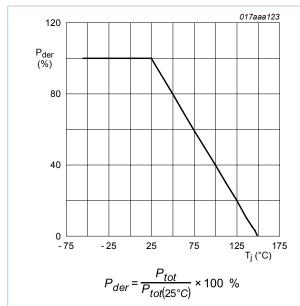


Fig. 1. Normalized total power dissipation as a function of junction temperature

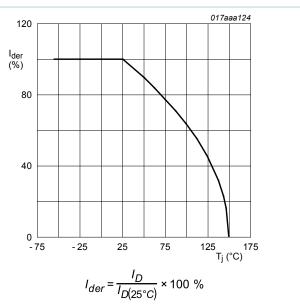
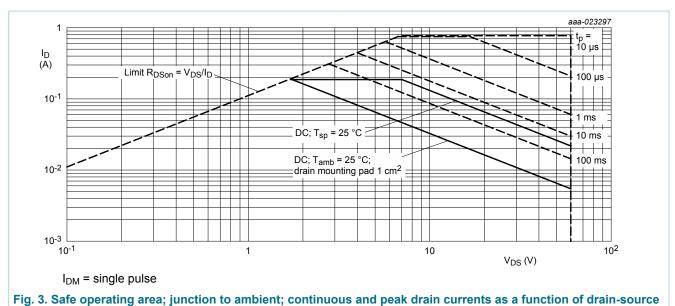


Fig. 2. Normalized continuous drain current as a function of junction temperature

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voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	410	470	K/W
			[2]	-	330	380	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	80	95	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².

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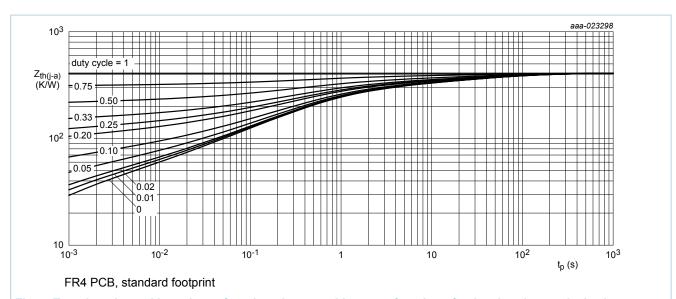


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

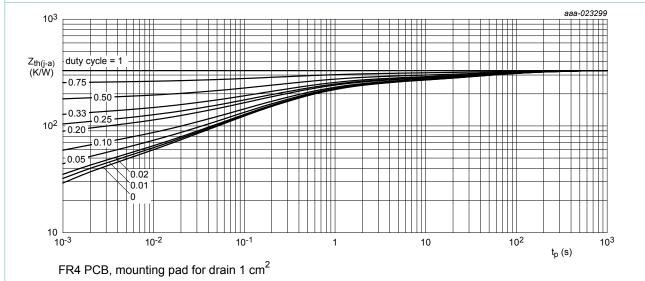


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			'		-
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} =V _{GS} ; T _j = 25 °C	0.8	1.1	1.5	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.5	μA
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
200	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 190 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	3	4.5	Ω
	resistance	V _{GS} = 10 V; I _D = 190 mA; T _j = 150 °C	-	6	9	Ω
		V _{GS} = 5 V; I _D = 170 mA; T _j = 25 °C	-	4	5.2	Ω
		$V_{GS} = 2.5 \text{ V}; I_D = 130 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	5	10	Ω
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 180 mA; T _j = 25 °C	-	3.5	-	S
Dynamic ch	naracteristics		'	-		
Q _{G(tot)}			-	0.9	1.4	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	15	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.3	-	pF
C _{rss}	reverse transfer capacitance		-	1.5	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; I _D = 190 mA; V _{GS} = 10 V;	-	8	12	ns
t _r	rise time	$R_{G(ext)} = 75 \Omega; T_j = 25 °C$	-	10	-	ns
$t_{d(off)}$	turn-off delay time		-	8	20	ns
t _f	fall time		-	5	-	ns
Source-dra	in diode			1	1	
V_{SD}	source-drain voltage	I _S = 190 mA; V _{GS} = 0 V; T _j = 25 °C	-	0.8	1.2	V
		•				

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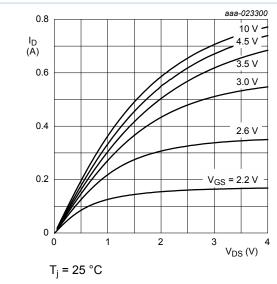


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

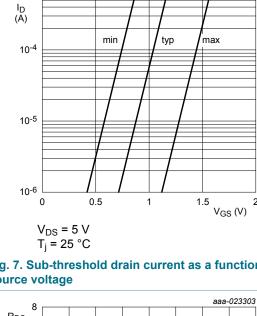


Fig. 7. Sub-threshold drain current as a function of gatesource voltage

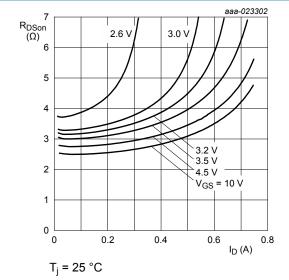


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

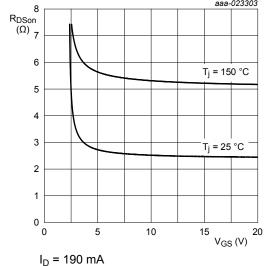


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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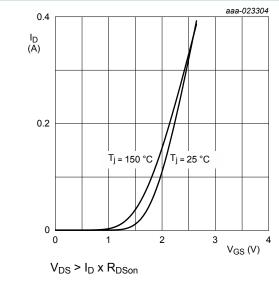


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

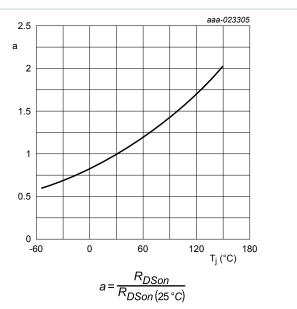


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

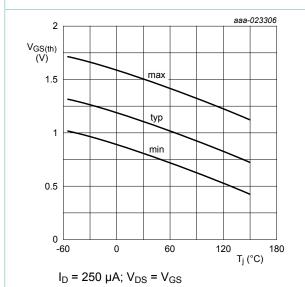


Fig. 12. Gate-source threshold voltage as a function of junction temperature

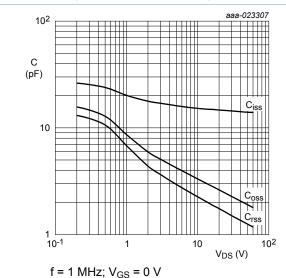


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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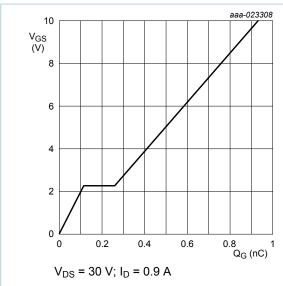


Fig. 14. Gate-source voltage as a function of gate charge; typical values

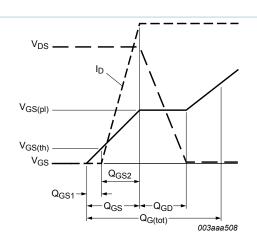


Fig. 15. MOSFET transistor: Gate charge waveform definitions

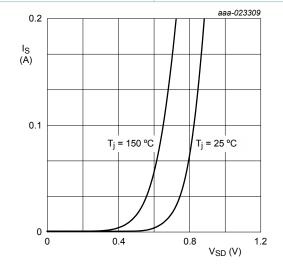
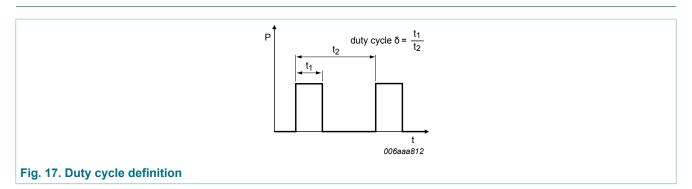


Fig. 16. Source current as a function of source-drain voltage; typical values

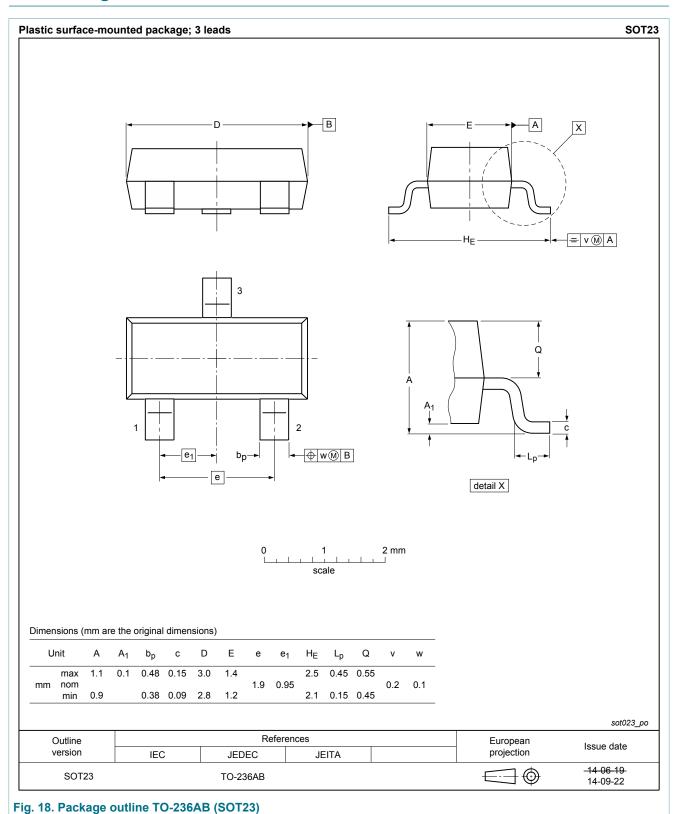
11. Test information

 $V_{GS} = 0 V$



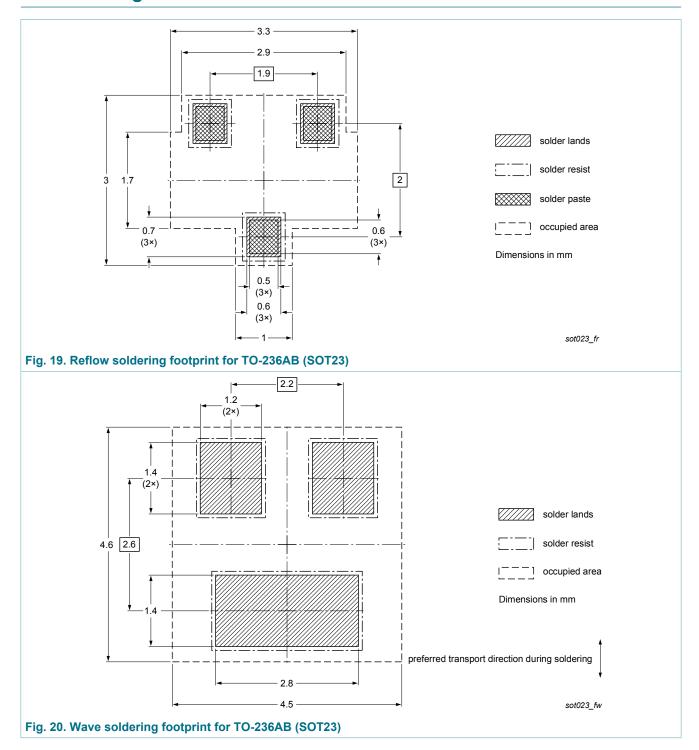
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
NX138AK v.2	20160610	Product data sheet	-	NX138AK v.1				
Modifications:	Title changed f	Title changed for figures 11 and 12 to juction temperature						
NX138AK v.1	20160607	Product data sheet	-	-				

60 V, N-channel Tench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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